FIG. 1A

Prior Art

Wafer loaded into chamber

Wafer ramped to temperature in N₂/O₂ mixture

SiO2 layer grown in steam

Wafer cooled and removed from reactor

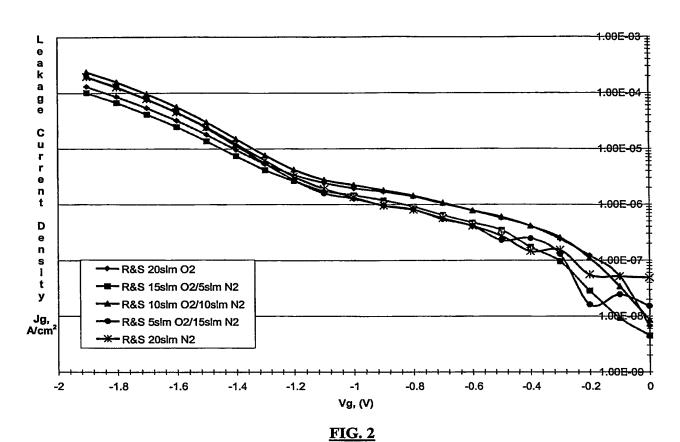
FIG. 1B

Present Invention

Wafer loaded into chamber

Wafer ramped to temperature in steam and SiO2 layer grown in steam

Wafer cooled and removed from reactor



Leakage Current Density vs Vgs Charts for 900°C Wet Oxidation Using Various Oxygen Flows During Ramp & Stabilization Step as practiced in the prior art.

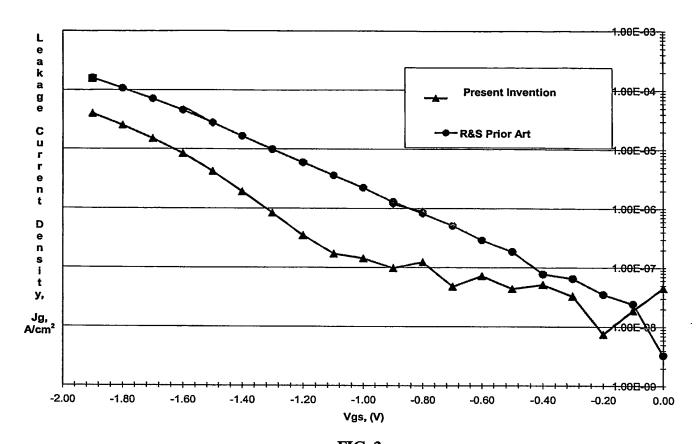


FIG. 3

Leakage current density (Jg) vs Vgs for wet oxidation processes at different process temperatures.

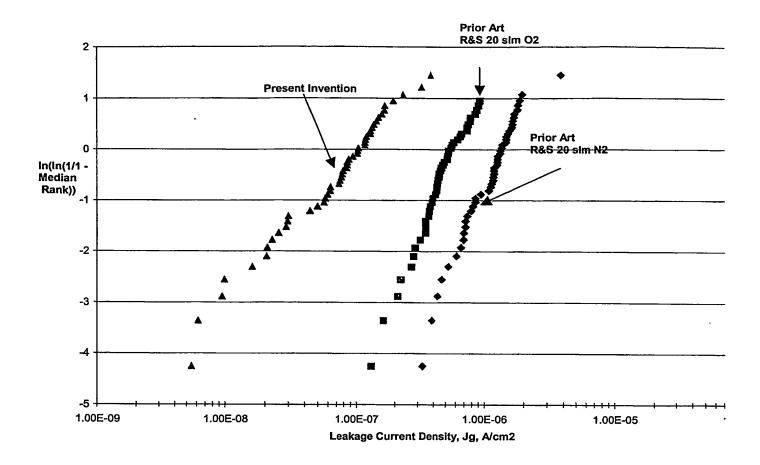


FIG. 4
Weibull plots for wet oxidation processes with and without ramp and stabilization step at 900°C